

SuperMOS – PDFN3X3-8L 30V BV_{DSS} 4m Ω $R_{DS(on)}$ 45A I_D , N-channel MOSFET

1. Description

The ESN7534 is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product ESN7534 is Pb-free.

2. Features

- 30V, $R_{DS(ON)}=4.0m\Omega(Typ)$, $V_{GS}=10V$
- $R_{DS(ON)}=6.5m\Omega(Typ)$, $V_{GS}=4.5V$
- Use trench MOSFET technology
- High density cell design for low $R_{DS(on)}$
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

3. Applications

- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

4. Ordering Information

Part Number	Package	Marking	Material	Packing	Quantity per reel	Flammability Rating	Reel Size
ESN7534	PDFN3X3-8L	.ESN7534/lot	Halogen free	Tape & Reel	5,000 PCS	UL 94V-0	13 inches

Table-1 Ordering information

5. Pin Configuration and Functions

Pin	Function	Outline	Circuit Diagram
4	Gate		
1/2/3	Source		
5/6/7/8	Drain		

Table-2 Pin configuration

6. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	BV_{DSS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	$T_C=25^\circ\text{C}$	45
		$T_C=75^\circ\text{C}$	35
Maximum Power Dissipation	P_D	$T_C=25^\circ\text{C}$	30
		$T_C=75^\circ\text{C}$	18
Pulsed Drain Current ^a	I_{DM}	180	A
Operating Junction Temperature	T_J	150	°C
Lead Temperature	T_L	260	°C
Storage Temperature Range	T_{stg}	-55 to 150	°C

Thermal resistance ratings

Single Operation				
Parameter		Symbol	Typical	Unit
Junction-to-Ambient Thermal Resistance	$t \leq 10 \text{ s}$	$R_{\theta JA}$	40	°C/W
Junction-to-Case Thermal Resistance	Steady State	$R_{\theta JC}$	4.2	

Note:

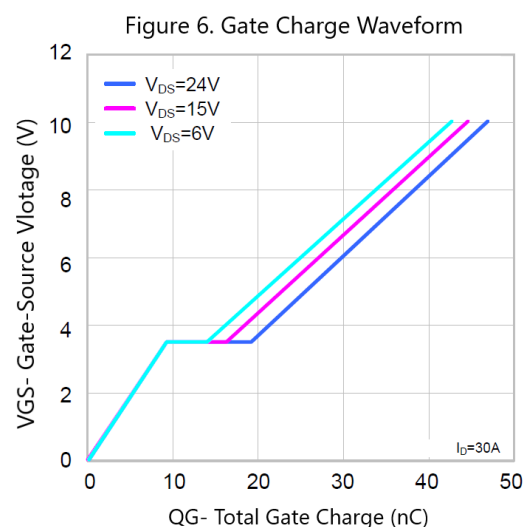
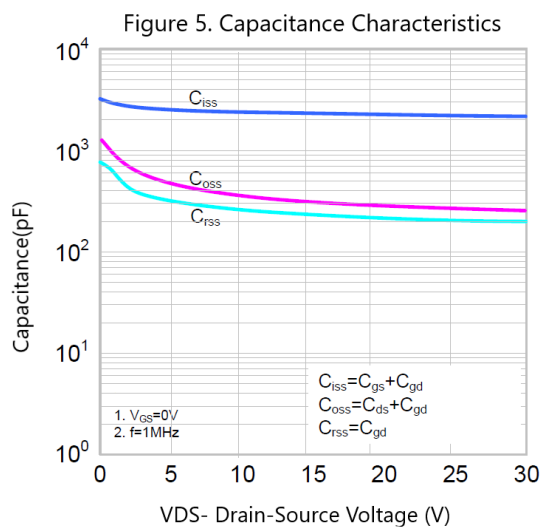
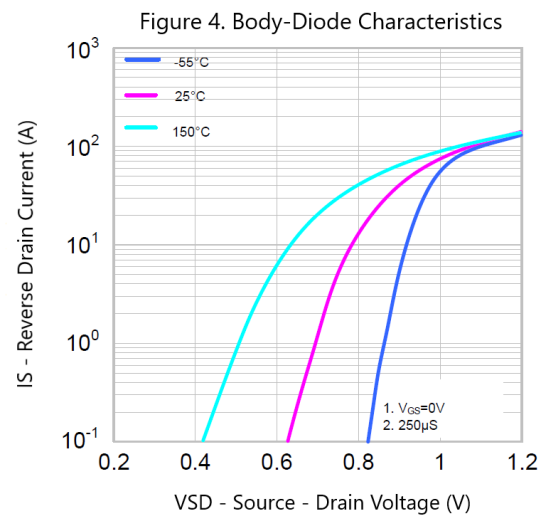
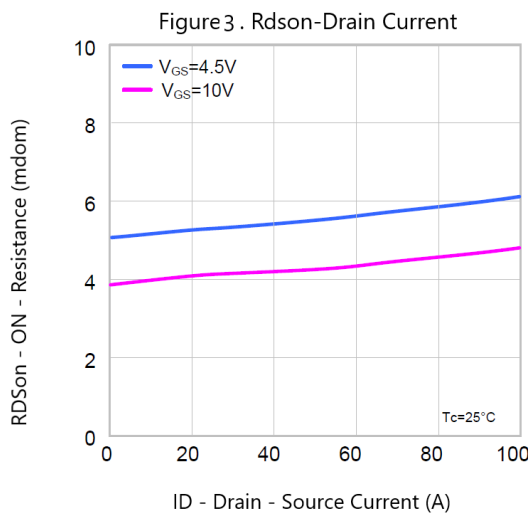
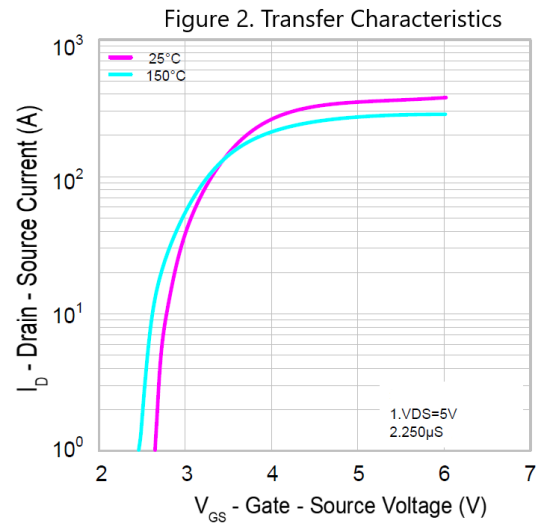
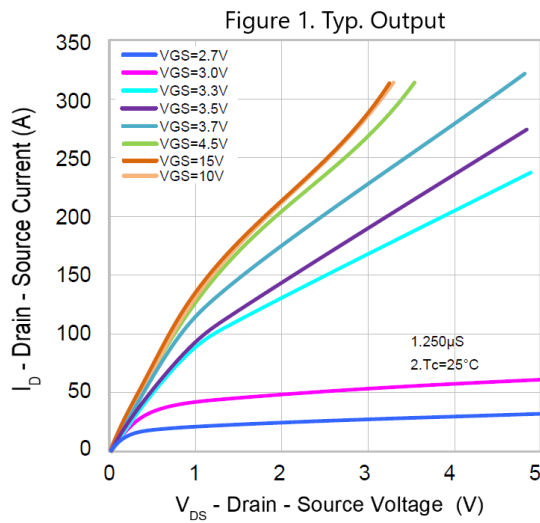
a: Repetitive rating, pulse width limited by junction temperature, $t_p=10\mu\text{s}$, Duty Cycle=1%

Electrical Characteristics

At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$			1.0	μA
Gate-to-source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 20V$			± 100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0	1.75	2.5	V
Drain-to-source On-resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$		4.0	7.5	m Ω
		$V_{GS}=4.5V, I_D=16A$		6.5	9.5	
Forward Trans conductance	g_{FS}	$V_{DS}=5.0V, I_D=10A$		25	40	S
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C_{ISS}	$V_{GS}=0V, f=1MHz, V_{DS}=25V$		2200		pF
Output Capacitance	C_{OSS}			275		
Reverse Transfer Capacitance	C_{RSS}			242		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS}=10V, V_{DS}=24V, I_D=30A$		48		nC
Gate-to-Source Charge	Q_{GS}			8.8		
Gate-to-Drain Charge	Q_{GD}			10.0		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{d(ON)}$	$V_{GS}=4.5V, V_{DS}=20V, I_D=60A, R_G=1.8\Omega$		12.5		ns
Rise Time	t_r			90		
Turn-Off Delay Time	$t_{d(OFF)}$			142		
Fall Time	t_f			85		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=1.0A$		0.75	1.5	V

7. Typical Characteristic



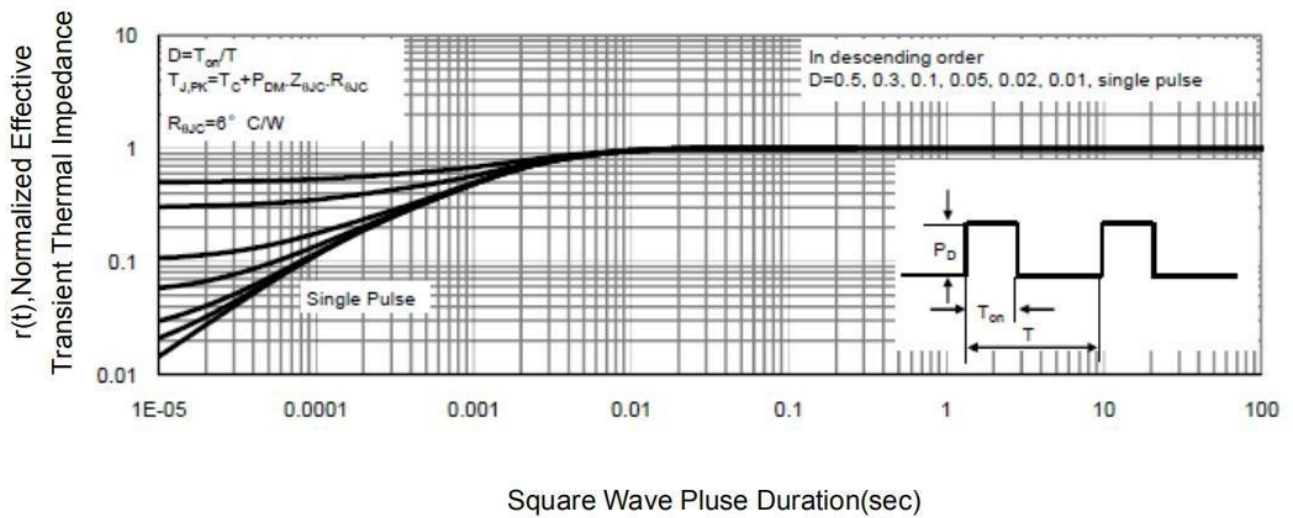
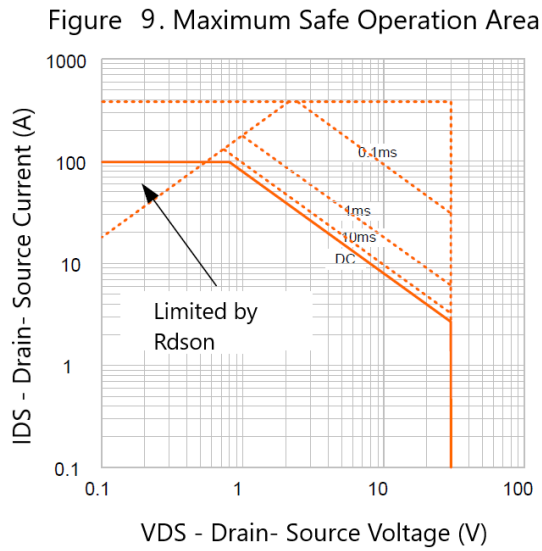
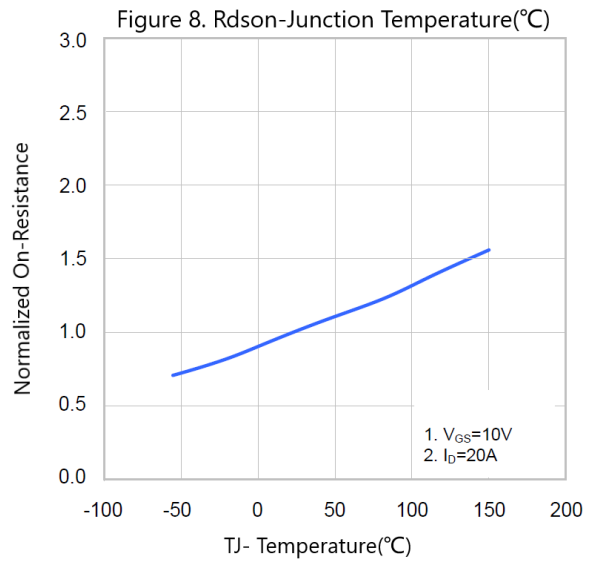
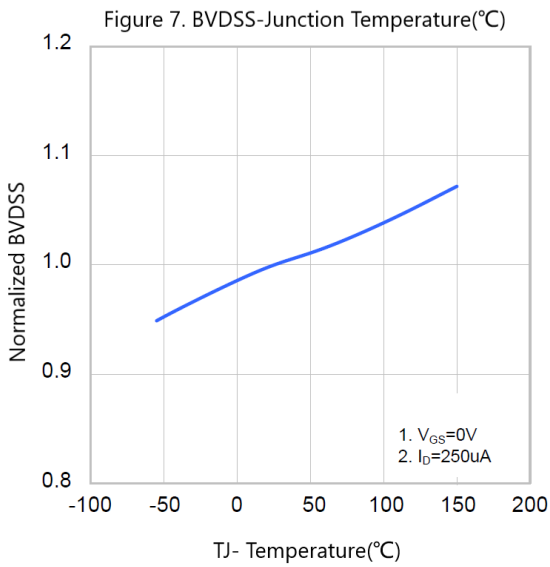
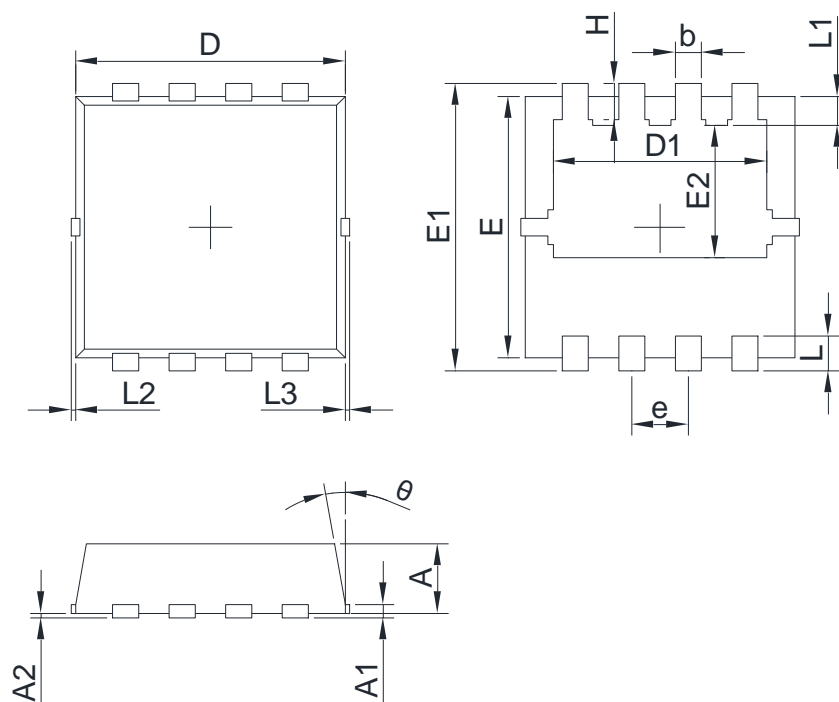


Figure 10 Normalized Maximum Transient Thermal Impedance

8. Dimension (PDFN3X3-8L)



Unit: mm

COMMON DIMENSIONS: UNITS OF MEASURE=MILLIMETER

SYMBOL	MILLIMETER			SYMBOL	MILLIMETER		
	MIN	Typ.	MAX		MIN	Typ.	MAX
A	0.700	0.800	0.900	b	0.200	0.300	0.400
A1	0.152 REF.			e	0.550	0.650	0.750
A2	0~0.05			L	0.300	0.400	0.500
D	3.000	3.100	3.200	L1	0.180	0.330	0.480
D1	2.300	2.450	2.600	L2	0~0.100		
E	2.900	3.000	3.100	L3	0~0.100		
E1	3.150	3.300	3.450	H	0.315	0.415	0.515
E2	1.320	1.520	1.720	theta	8°	10°	12°

Table-5 Product dimensions in millimeter

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